

# Kun Yang

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Interface optimization of La-based gate dielectric for molybdenum disulfide field-effect transistors. Applied Surface Science, 2022, 581, 152248.	3.1	3
2	Synthesis and Spectral Characteristics Investigation of the 2D-2D vdWs Heterostructure Materials. International Journal of Molecular Sciences, 2021, 22, 1246.	1.8	2
3	Investigation of charge trapping mechanism in MoS <sub>2</sub> field effect transistor by incorporating Al into host La <sub>2</sub> O <sub>3</sub> as gate dielectric. Nanotechnology, 2021, 32, 305201.	1.3	5
4	Low-Power OR Logic Ferroelectric In-Situ Transistor Based on a CuInP2S6/MoS2 Van Der Waals Heterojunction. Nanomaterials, 2021, 11, 1971.	1.9	5
5	Preparation and Research of Monolayer WS2 FETs Encapsulated by h-BN Material. Micromachines, 2021, 12, 1006.	1.4	5
6	Comprehensive Performance Quasi-Non-Volatile Memory Compatible with Large-Scale Preparation by Chemical Vapor Deposition. Nanomaterials, 2020, 10, 1471.	1.9	4
7	The Large-Scale Preparation and Optical Properties of MoS2/WS2 Vertical Hetero-Junction. Molecules, 2020, 25, 1857.	1.7	7
8	Research on the Preparation and Spectral Characteristics of Graphene/TMDs Hetero-structures. Nanoscale Research Letters, 2020, 15, 219.	3.1	8
9	Probing the Field-Effect Transistor with Monolayer MoS2 Prepared by APCVD. Nanomaterials, 2019, 9, 1209.	1.9	10
10	A Horizontal-Gate Monolayer MoS2 Transistor Based on Image Force Barrier Reduction. Nanomaterials, 2019, 9, 1245.	1.9	10
11	Probing the Optical Properties of MoS2 on SiO2/Si and Sapphire Substrates. Nanomaterials, 2019, 9, 740.	1.9	25
12	Design and Investigation of the Junction-Less TFET with Ge/Si0.3Ge0.7/Si Heterojunction and Heterogeneous Gate Dielectric. Electronics (Switzerland), 2019, 8, 476.	1.8	14
13	Design and investigation of dopingless dual-gate tunneling transistor based on line tunneling. AIP Advances, 2019, 9, .	0.6	10